

X-736 US
10/079,235

Patent
Conf. No.: 7201

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

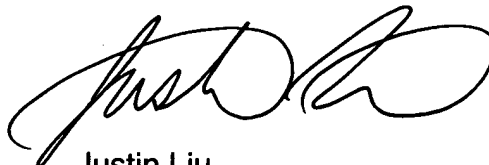
Applicant: Robert O. Conn
Assignee: Xilinx, Inc.
Title: "Method to Produce a Factory Programmable IC Using Standard IC
Wafers and the Structure"
Serial No.: 10/079,235 Filing Date: February 19, 2002
Examiner: Shouxiang Hu Art Unit: 2811
Docket No.: X-736 US Conf. No.: 7201

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Amendment Pursuant to 37 CFR 1.312

Pursuant to 37 CFR 1.312, Applicant respectfully requests entry of the following amendment to correct a minor formal matter. Applicant requests that the first word on line 19, in Claim 6, on page 3 of the Examiner's Amendment be changed from "merger" to --merge--. A copy of Claim 6 marked to show the requested amendment is attached hereto.

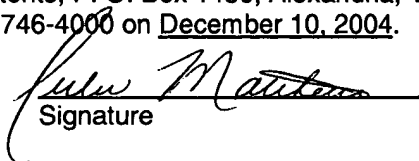
Respectfully submitted,



Justin Liu
Attorney for Applicant
Reg. No.: 51,959
(408) 879-4641

I hereby certify that this correspondence is being sent **via US Mail** to:
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Julie Matthews
Name


Signature

Listing of Claim 6, marked to show the requested amendment

6. A method for altering the semiconductor characteristics of a semiconductor element formed on a substrate, the method comprising:

- directing an energy beam at the semiconductor element, wherein the energy beam is substantially absorbed by a first portion of the semiconductor element;
- thinning the substrate under the semiconductor element; and
- the step of directing an energy beam at the semiconductor element including directing the energy beam at the first portion of the semiconductor element through the substrate, wherein the energy beam is substantially transmitted through the substrate;

wherein the semiconductor element comprises:

- a source region;
- a drain region;
- a channel region between the source region and the drain region;
- a gate oxide formed over the channel region; and
- a gate formed over the gate oxide, wherein the first portion of the semiconductor element comprises the gate, and wherein the energy beam is substantially transmitted through the channel region; and

wherein the energy beam causes the source region and the drain region to ~~merge~~merge so as to form an always-on current path in the semiconductor element.